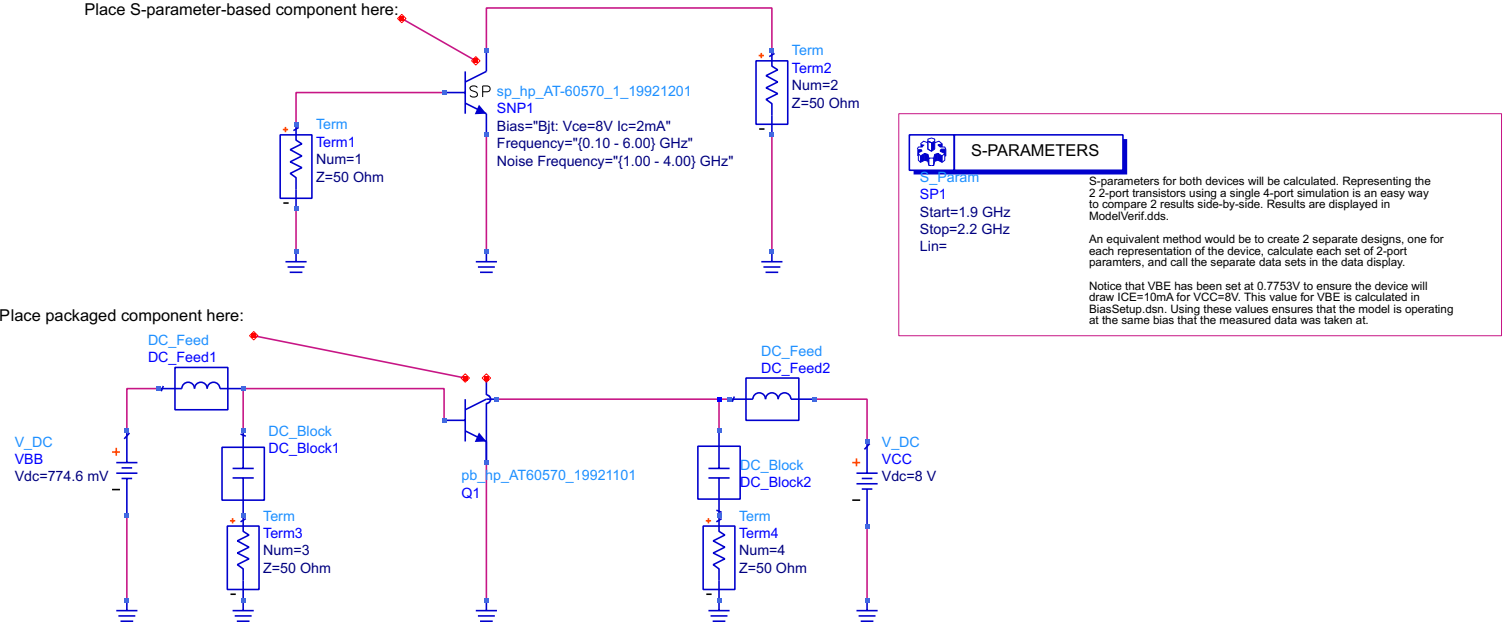
Place S-parameter-based component here:
Term
Term1
Num=1
Z=50 Ohm
SP
sp_hp_AT-60570_1_19921201
SNP1
Bias="Bjt: Vce=8V Ic=2mA"
Frequency="{0.10 - 6.00} GHz"
Noise Frequency="{1.00 - 4.00} GHz"
Term
Term2
Num=2
Z=50 Ohm
S-PARAMETERS
S_Param
SP1
Start=1.9 GHz
Stop=2.2 GHz
Lin=
S-parameters for both devices will be calculated. Representing the 2 2-port transistors using a single 4-port simulation is an easy way to compare 2 results side-by-side. Results are displayed in ModelVerif.dds.
An equivalent method would be to create 2 separate designs, one for each representation of the device, calculate each set of 2-port paramters, and call the separate data sets in the data display.
Notice that VBE has been set at 0.7753V to ensure the device will draw ICE=10mA for VCC=8V. This value for VBE is calculated in BiasSetup.dsn. Using these values ensures that the model is operating at the same bias that the measured data was taken at.
Place packaged component here:
DC_Feed
DC_Feed1
V_DC
VBB
Vdc=774.6 mV
DC_Block
DC_Block1
Term
Term3
Num=3
Z=50 Ohm
pb_hp_AT60570_19921101
Q1
DC_Feed
DC_Feed2
DC_Block
DC_Block2
Term
Term4
Num=4
Z=50 Ohm
V_DC
VCC
Vdc=8 V